

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3264282	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:04
L2	2484	1 and (charge or electron or hole) with between with floating adj gate with control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:12
L3	290	2 and high near5 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:35
L4	160	3 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:12
L5	85	4 and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:13
L6	85	1 and (charge or electron or hole) with between with floating adj gate with control adj gate with (via or through) with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:12
L7	39	6 and silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:12
L8	25	7 and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:19
L9	10	8 and high near5 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:19
L10	14	2 and high near5 dielectric with floating adj gate with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:46
L11	15	1 and high near5 k near3 dielectric with floating adj gate with substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/10/30 19:47